



DMN6010SCTB

## **Product Summary**

BV <sub>DSS</sub>	BV <sub>DSS</sub> R <sub>DS(ON)</sub> Max I <sub>D</sub> Ma T <sub>C</sub> = +2	
60V	10mΩ @ V <sub>GS</sub> = 10V	128A

# **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance (R<sub>DS(on)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Controls
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

## 60V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R<sub>DS(on)</sub> Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

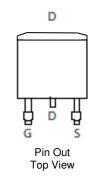
## **Mechanical Data**

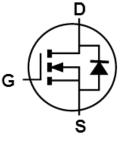
- Package: TO263AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.7 grams (Approximate)



TO263AB (D2PAK)

Top View





Internal Schematic

### Ordering Information (Note 4)

Part Number	Backago	Packing		
Part Number	Package	Qty.	Carrier	
DMN6010SCTB-13	TO263AB (D2PAK)	800	Reel	

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**



Dil = Manufacturer's Marking N6010SCT = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 21 = 2021) WW = Week (01 to 53)

# Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	Vgss	±20	V	
	T <sub>C</sub> = +25°C		128	^
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	$T_{\rm C} = +70^{\circ}{\rm C}$	ID -	102	A
Maximum Continuous Body Diode Forward Current (Note 6)	Tc = +25°C	ls	128	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	512	А	
Avalanche Current, L =0.1mH		las	71	А
Avalanche Energy, L = 0.1mH		Eas	252	mJ

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	PD	5	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	30	°C/W
Total Power Dissipation (Note 6)	TC = +25°C	PD	312	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0</sub> JC	0.4	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:

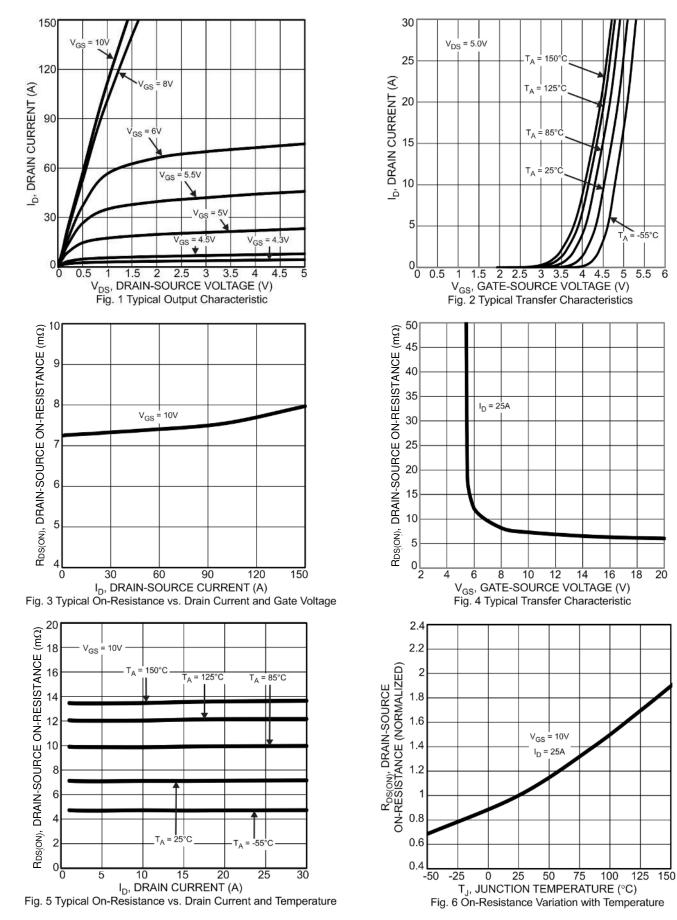


## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

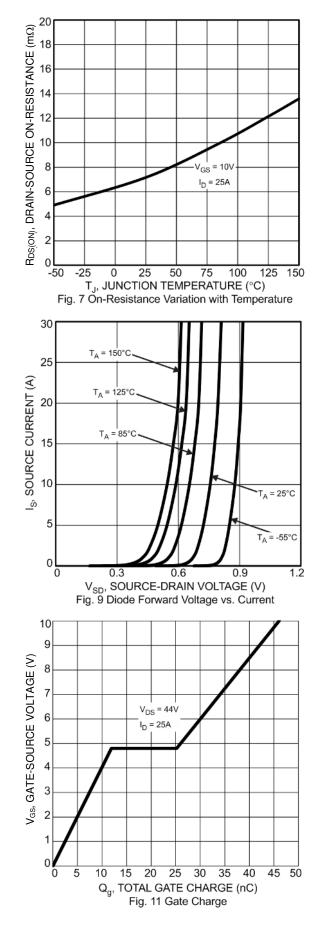
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	10	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	2	-	4	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	7.7	10	mΩ	$V_{GS}=10V,\ I_D=25A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 25A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	—	2692			V <sub>DS</sub> =25V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	—	909	_	pF		
Reverse Transfer Capacitance	Crss	_	65	_			
Gate Resistance	Rg	—	3.6		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	—	46	_			
Gate-Source Charge	Qgs	_	12	_	nC	V <sub>DS</sub> = 44V, I <sub>D</sub> = 25A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	Qgd	_	13	_		VGS = 10V	
Turn-On Delay Time	tD(on)	_	13.5	_			
Turn-On Rise Time	tR	_	44	_	ns	$\label{eq:VDS} \begin{split} V_{DS} &= 30V, \ V_{GEN} = 10V, \\ R_L &= 1.2\Omega \end{split}$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	45	_			
Turn-Off Fall Time	tF	_	29	_	]		
Reverse Recovery Time	trr	_	51.5	_	ns	IF = 20A, di/dt = 100A/µs,	
Reverse Recovery Charge	Q <sub>RR</sub>		92		nC	V <sub>R</sub> = 30V	

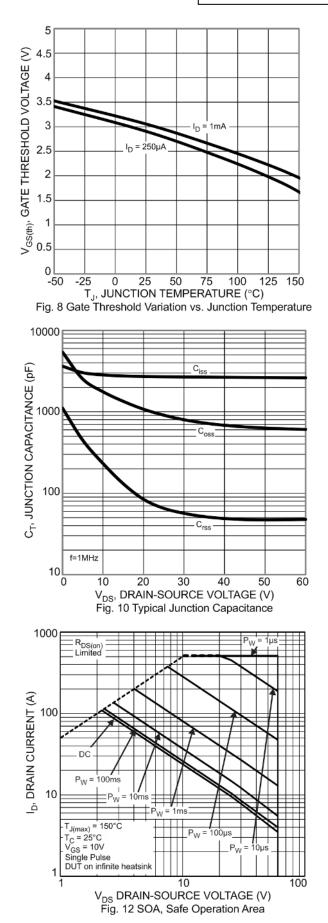
 Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:





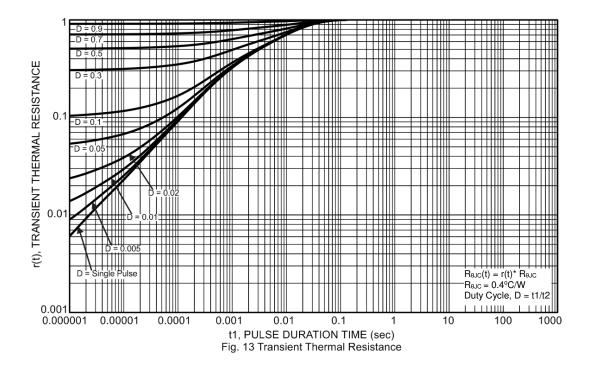






DMN6010SCTB Document number: DS43782 Rev. 2 - 2

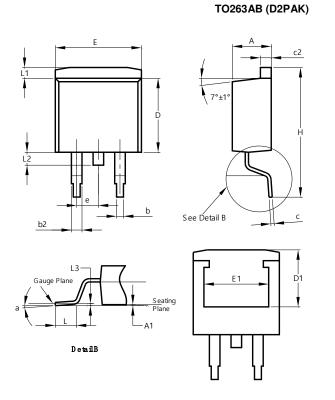






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

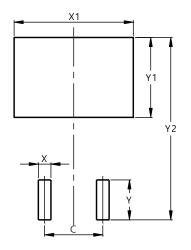


то	TO263AB (D2PAK)				
Dim	Min	Max	Тур		
Α	4.07	4.82	-		
A1	0.00	0.25	-		
b	0.51	0.99	-		
b2	1.15	1.77	-		
С	0.356	0.73	-		
c2	1.143	1.143 1.65 -			
D	8.39	9.65	-		
D1	6.55	6.95	-		
e		2.54 TYP			
Е	9.66	10.66	-		
E1	6.23	8.23	-		
H	14.61	15.87	-		
L	1.78	2.79	-		
L1	-	1.67	-		
L2	-	1.77	-		
L3	-	-	0.254		
а	0°	8°	-		
All D	All Dimensions in mm				

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO263AB (D2PAK)



Dimensions	Value (in mm)			
C	5.08			
Х	1.10			
X1	10.41			
Y	3.50			
Y1	7.01			
Y2	15.99			



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